

Description

The HXY3404MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



General Features

 $V_{DS} = 30V I_D = 5A$

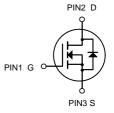
 $R_{DS(ON)}$ < 28m Ω @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3404MI	SOT23-3L	X4HV	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

symbol	parameter	limit	unit
V _{DS}	Drain-source voltage	30	V
V _{GS}	Gate-source voltage	±20	V
ID	Drain current-continuousª@Tj=125°C		А
IDM	-pulse d ^b	20	А
ls	Drain-source Diode forward current	5	А
P _D	Maximum power dissipation	1.4	W
Tj	Operating junction Temperature range	-55—150	°C
Rth JA	Thermal Resistance junction-to ambient	100	°C/W



Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Condition	Min	Тур	Max	Unit
BV _{DSS}	V _{GS} =0V, I _D =250μA	30	-	-	V
IDSS	V _{DS} =30V, V _{GS} =0V	-	-	1	μΑ
IGSS	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
VGS(th)	V _{DS} =V _{GS} , I _D =250µA	0.8	1.4	2.2	V
	V _{GS} =10V, I _D =5A	-	24	28	
RDS(ON)	V _{GS} =4.5V, I _D =4A		26	32	mΩ
gfs	V _{GS} =5V, I _D =5A	-	33	-	S
C _{ISS}	V _{DS} =15V_V _{GS} =0V		255		pF
coss	f=1.0MHz		45		
CRSS			35		
tD(ON)		-	4.5	-	- ns
tr	V _{DS} =15V V _{GS} =10V	-	2.5	-	
tD(OFF)	R _L =2.6 ohm R _{GEN} =3ohm	-	14.5	-	
tf		-	3.5	-	
Qg		-	5.2	-	
Qgs	V _{DS} =15V,I _D =5.8A	-	0.85	-	nC
Qgd	V _{GS} =10V	-	1.3	-	
					V
	BV _{DSS} IDSS IGSS VGS(th) RDS(ON) gfs Clss COSS CRSS tD(ON) tr tD(OFF) tf Qg Qgs	BV _{DSS} V _{GS} =0V, I _D =250μA IDSS V _{DS} =30V, V _{GS} =0V IGSS V _{DS} =0V, V _{GS} =±20V VGS(th) V _{DS} =V _{GS} , I _D =250μA V _{GS} =10V, I _D =5A RDS(ON) V _{GS} =4.5V, I _D =4A V _{GS} =5V, I _D =5A C _{ISS} V _{DS} =15V, V _{GS} =0V f=1.0MHz CRSS tD(ON) tr V _{DS} =15V V _{GS} =10V R _L =2.6 ohm R _{GEN} =3ohm tf Qg Qgs V _{DS} =15V, I _D =5.8A V _{GS} =10V	BV _{DSS} V _{GS} =0V, I _D =250μA 30 IDSS V _{DS} =30V, V _{GS} =0V - IGSS V _{DS} =0V, V _{GS} =±20V - VGS(th) V _{DS} =V _{GS} , I _D =250μA 0.8 RDS(ON) V _{GS} =10V, I _D =5A - V _{GS} =4.5V, I _D =4A - C _{ISS} V _{DS} =15V, V _{GS} =0V f=1.0MHz Tr V _{DS} =15V V _{GS} =10V R _L =2.6 ohm R _{GEN} =3ohm - Qg - Qgs V _{DS} =15V, I _D =5.8A - Qgs V _{DS} =15V, I _D =5.8A - C _{GS} =10V -	BV _{DSS} V _{GS} =0V, I _D =250μA 30 - IDSS V _{DS} =30V, V _{GS} =0V IGSS V _{DS} =0V, V _{GS} =±20V VGS(th) V _{DS} =V _{GS} , I _D =250μA 0.8 1.4 V _{GS} =10V, I _D =5A - 24 RDS(ON) V _{GS} =4.5V, I _D =4A 26 gfs V _{GS} =5V, I _D =5A - 33 C _{ISS} V _{DS} =15V, V _{GS} =0V f=1.0MHz 45 CRSS 35 tD(ON) tr V _{DS} =15V V _{GS} =10V R _L =2.6 ohm R _{GEN} =3ohm - 14.5 Qg - 5.2 Qgs V _{DS} =15V,I _D =5.8A - 0.85	BV _{DSS} V _{GS} =0V, I _D =250μA 30 1 IDSS V _{DS} =30V, V _{GS} =0V 1 IGSS V _{DS} =0V, V _{GS} =±20V ±100 VGS(th) V _{DS} =V _{GS} , I _D =250μA 0.8 1.4 2.2 V _{GS} =10V, I _D =5A - 24 28 RDS(ON) V _{GS} =4.5V, I _D =4A 26 32 gfs V _{GS} =5V, I _D =5A - 33 - 255 C _{ISS} V _{DS} =15V, V _{GS} =0V f=1.0MHz 45 CRSS 35 tD(ON) tr V _{DS} =15V V _{GS} =10V R _L =2.6 ohm R _{GEN} =3ohm R _{GEN} =3ohm tf - 3.5 - 0.85 - 0.85 Qg V _{DS} =15V, I _D =5.8A V _{GS} =10V - 5.2 - 0.85 Qg - 5.2 - 0.85 - 0.85

Notes:

- 1、surface mounted on FR4 board,t≤10sec
- 2、pulse test: pulse width≤300µs,duty≤2%
- 3. guaranteed by design, not subject to production testing



Typical Performance Characteristics

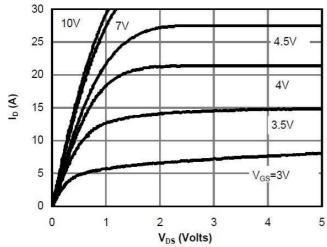
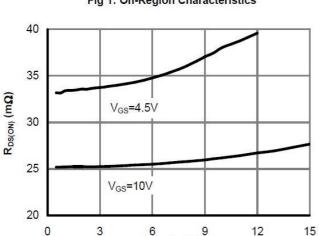


Fig 1: On-Region Characteristics



I_D (A)
Figure 3: On-Resistance vs. Drain Current and
Gate Voltage

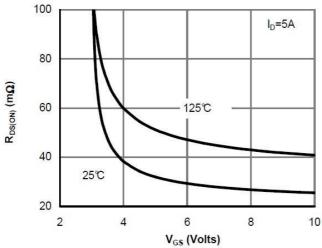


Figure 5: On-Resistance vs. Gate-Source Voltage

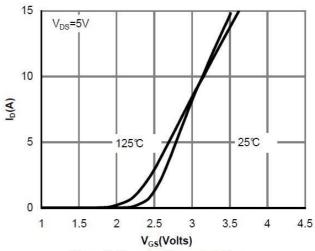


Figure 2: Transfer Characteristics

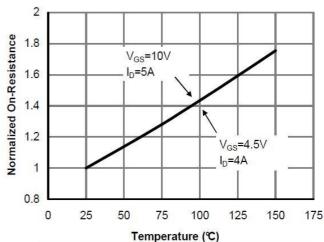


Figure 4: On-Resistance vs. Junction Temperature

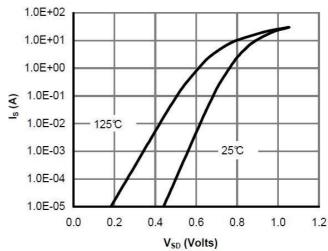
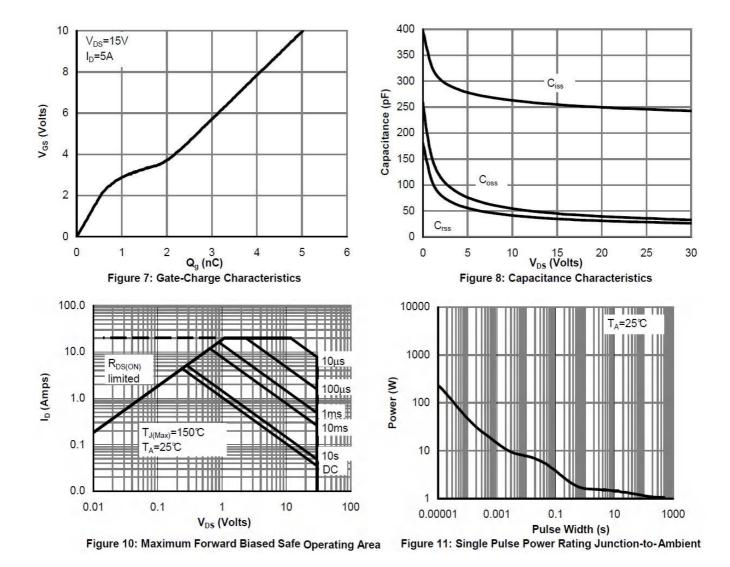


Figure 6: Body-Diode Characteristics





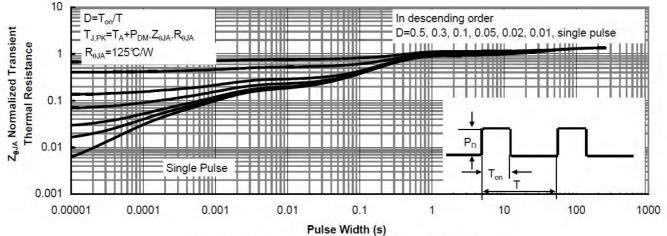
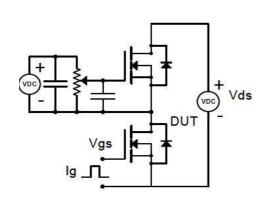
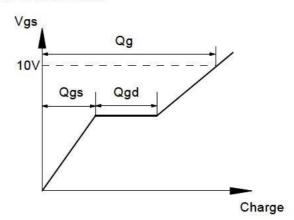


Figure 12: Normalized Maximum Transient Thermal Impedance



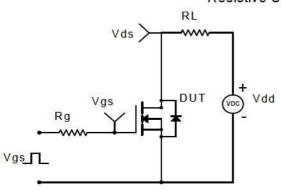
Gate Charge Test Circuit & Waveform

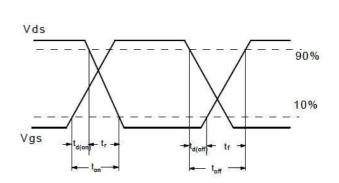




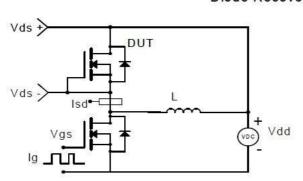
Resistive Switching Test Circuit & Waveforms

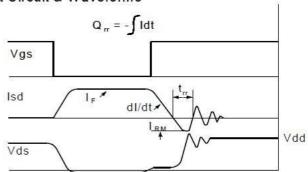
Resistive Switching Test Circuit & Waveforms



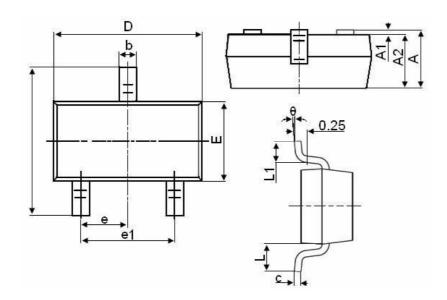


Diode Recovery Test Circuit & Waveforms





SOT23-3L Package Information



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.600		
θ	0°	8°		

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